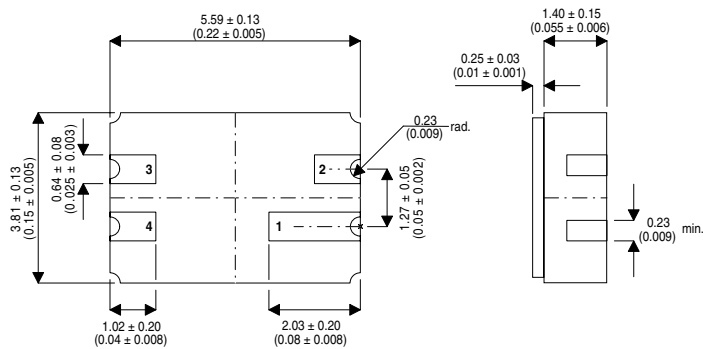


MECHANICAL DATA

Dimensions in mm (inches)


LCC3

PAD 1 = COLLECTOR PAD 3 = EMITTER
 PAD 2 = N/C PAD 4 = BASE

SILICON PLANAR NPN HIGH VOLTAGE TRANSISTOR IN A CERAMIC SURFACE MOUNT PACKAGE
FEATURES

- High Voltage
- Ceramic Surface Mount
- Screening Options Available

ABSOLUTE MAXIMUM RATINGS

V_{CBO}	Collector - Base Voltage ($I_E = 0$)	160V
V_{CEO}	Collector - Emitter Voltage ($I_B = 0$)	160V
V_{EBO}	Emitter Base Voltage ($I_C = 0$)	5V
I_C	Collector Current	100mA
I_{CM}	Collector Peak Current	200mA
P_{tot}	Total Power Dissipation at $T_{case} \leq 50^\circ C$	5W
T_{stg}	Storage Temperature	-55 to 200°C
T_j	Junction Temperature	200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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Thermal Data

$R_{th\ j-case}$	Thermal resistance junction - case	max	30°C/W
$R_{th\ j-amb}$	Thermal resistance junction - ambient	max	175°C/W

Electrical Characteristics

($T_{amb} = 25^{\circ}C$ Unless otherwise specified)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{(BR)CEO}^*$	Collector–Emitter Breakdown Voltage	$I_C = 10mA$	$I_B = 0$	160	V	
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	$I_C = 100\mu A$	$I_E = 0$	160		
$V_{(BR)EBO}$	Emitter - Base Breakdown Voltage	$I_C = 0$	$I_E = 100\mu A$	5		
I_{CBO}	Collector Cutoff Current	$V_{CB} = 100V$	$I_E = 0$		50	nA
$V_{CE(sat)}^*$	Collector – Emitter Saturation Voltage	$I_C = 30mA$	$I_B = 6mA$		1	V
h_{FE}^*	DC Current Gain	$I_C = 30mA$	$I_B = 10V$	25		—
f_t	Transition Frequency	$I_C = 15mA$	$V_{CE} = 10V$		90	MHz
C_{re}	Reverse Capacitance	$I_C = 0$ $f = 1MHz$	$V_{CE} = 30V$		3	pF

* Pulsed test $t_p = 300\mu s$, $\delta = 1\%$